IN THE CLAIMS:

Please amend the claims as follows:

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1. (Amended) A semiconductor device structure having a [homogenous] <u>void-free</u>, <u>homogeneous</u> aluminum alloy material within contact holes in an insulating layer overlying a substrate, the semiconductor device structure formed by the method comprising:

depositing an aluminum material on an exposed surface of the insulating layer and over the contact holes;

heating the aluminum material to reflow the aluminum material into the contact holes so as to at least partially fill the contact holes;

applying pressure to the aluminum material to completely fill the contact holes; depositing a different metal material on the aluminum material over the contact holes; and

diffusing the different metal material into the aluminum material to form a homogeneous aluminum alloy fill material in the contact holes.

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23. (Amended) A semiconductor assembly formed by the method comprising:

providing a semiconductor substrate having an insulating layer overlying the

semiconductor substrate, the insulating layer having contact holes formed therein;

simultaneously depositing and heating an aluminum material an on outer surface of the

insulating layer and over the contact holes;

applying pressure to the aluminum material to completely fill the contact holes; depositing a different metal material on the aluminum material; and diffusing the different metal material into the aluminum material to form a substantially homogeneous void-free, aluminum alloy fill material in the contact holes.